

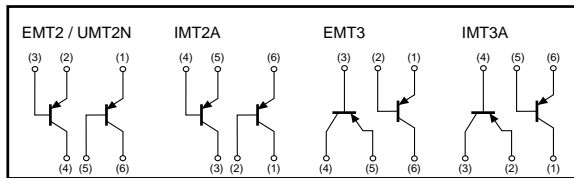
General purpose (dual transistors)

EMT2 / EMT3 / UMT2N / IMT2A / IMT3A

●Features

1) Two 2SA1037AK chips in a EMT or UMT or SMT package.

●Equivalent circuits



●Absolute maximum ratings (Ta=25°C)

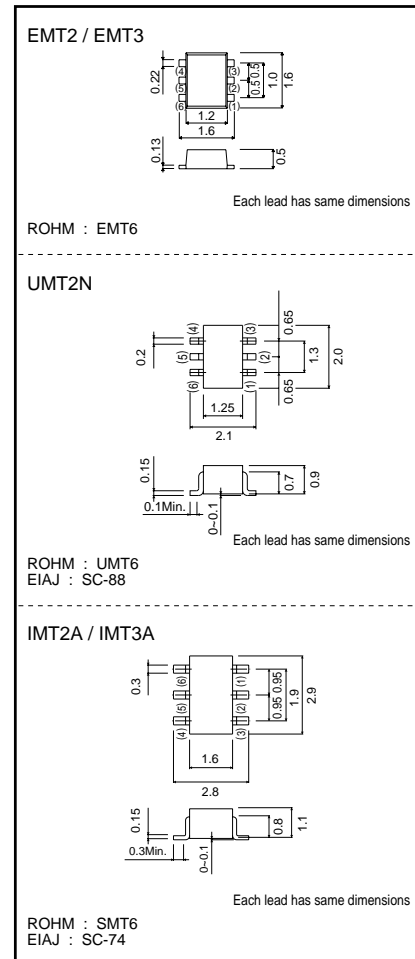
| Parameter | Symbol | Limits | Unit |
|-----------------------------|---------------------|------------|-------|
| Collector-base voltage | V _{CB0} | -60 | V |
| Collector-emitter voltage | V _{CEO} | -50 | V |
| Emitter-base voltage | V _{EBO} | -6 | V |
| Collector current | I _c | 150 | mA |
| Collector power dissipation | EMT2 / EMT3 / UMT2N | 150(TOTAL) | mW *1 |
| | IMT2A / IMT3A | 300(TOTAL) | |
| Junction temperature | T _j | 150 | °C |
| Storage temperature | T _{stg} | -55~+150 | °C |

*1 120mW per element must not be exceeded.
*2 200mW per element must not be exceeded.

●Package, marking, and packaging specifications

| Type | EMT2 | EMT3 | UMT2N | IMT2A | IMT3A |
|------------------------------|------|------|-------|-------|-------|
| Package | EMT6 | EMT6 | UMT6 | SMT6 | SMT6 |
| Marking | T2 | T3 | T2 | T2 | T3 |
| Code | T2R | T2R | TR | T108 | T108 |
| Basic ordering unit (pieces) | 8000 | 8000 | 3000 | 3000 | 3000 |

●External dimensions (Units : mm)



●Electrical characteristics (Ta=25°C)

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Conditions |
|--------------------------------------|----------------------|------|------|------|------|--|
| Collector-base breakdown voltage | BV _{CB0} | -60 | - | - | V | I _c =-50μA |
| Collector-emitter breakdown voltage | BV _{CEO} | -50 | - | - | V | I _c =-1mA |
| Emitter-base breakdown voltage | BV _{EBO} | -6 | - | - | V | I _E =-50μA |
| Collector cutoff current | I _{cBO} | - | - | -0.1 | μA | V _{CB} =-60V |
| Emitter cutoff current | I _{EBO} | - | - | -0.1 | μA | V _{EB} =-6V |
| Collector-emitter saturation voltage | V _{CE(sat)} | - | - | -0.5 | V | I _c /I _B =-50mA/-5mA |
| DC current transfer ratio | h _{FE} | 120 | - | 560 | - | V _{CE} =-6V, I _c =-1mA |
| Transition frequency | f _t | - | 140 | - | MHz | V _{CE} =-12V, I _E =2mA, f=100MHz * |
| Output capacitance | C _{ob} | - | 4 | 5 | pF | V _{CE} =-12V, I _E =0A, f=1MHz |

*Transition frequency of the device.